

# HiRel Silicon Schottky Diode

- *HiRel* Discrete and Microwave Semiconductor
- General-purpose diodes for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detecting and mixing
- Hermetically sealed microwave package
- CC CSA Space Qualified ESA/SCC Detail Spec. No.: 5512/020 Type Variant No. 03

**ESD**: Electrostatic discharge sensitive device, observe handling precautions!

Туре	Marking	Ordering Code	Pin Configuration	Package
BAS40-T1 (ql)	-	see below	12	T1

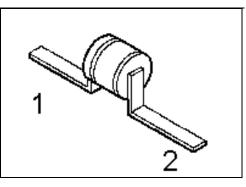
(ql) Quality Level: P: Professional Quality

H: High Rel Quality

S: Space Quality

ES: ESA Space Quality

(see order instructions for ordering example)





### **Maximum Ratings**

Parameter	Symbol	Values	Unit	
Reverse Voltage	V <sub>R</sub>	40	V	
Forward Current	I <sub>F</sub>	120	mA	
Surge Forward Current 1)	I <sub>FSM</sub>	170	mA	
Power Dissipation <sup>2)</sup>	P <sub>tot</sub>	250	mW	
Operating Temperature Range	T <sub>op</sub>	-55 to +150	°C	
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C	
Soldering Temperature <sup>3)</sup>	T <sub>sol</sub>	+250	°C	
Junction Temperature	T <sub>j</sub>	150	°C	
Thermal Resistance Junction-Case	R <sub>th(j-c)</sub>	100	K/W	

## **Electrical Characteristics**

at T<sub>A</sub>=25°C; unless otherwise specified

Parameter	Symbol		Values		Unit
		min.	typ.	max.	
DC Characteristics		•			
Reverse Current 1, V <sub>R</sub> =40V	I <sub>R1</sub>	-	-	10	μA
Reverse Current 2, V <sub>R</sub> =30V	I <sub>R2</sub>	-	-	1	μA
Forward Voltage 1, I <sub>F1</sub> =1mA	V <sub>F1</sub>	0,29	0,33	0,39	V
Forward Voltage 2, I <sub>F2</sub> =10mA	V <sub>F2</sub>	0,42	0,45	0,54	V
Forward Voltage 3, I <sub>F3</sub> =40mA	V <sub>F3</sub>	0,68	0,7	0,85	V
Differential Forward Resistance 4)	R <sub>FD</sub>	7,5	10	11,5	Ω
IF=10mA, IF=15mA					
AC Characteristics		•	•	•	

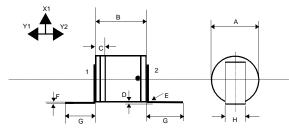
Total Capacitance	CT	2,2	2,9	5,0	pF
V <sub>R</sub> =0V; f=1MHz					

# Notes .:

1.) t  $\leq$  10ms, Duty Cycle=10% 2.) At T<sub>CASE</sub> = 125 °C. For T<sub>CASE</sub> > 125 °C derating is required. 3.) During 5 sec. maximum. The same terminal shall not be resoldered until 3 minutes have elapsed.







Symbol	Millimetre		
	min	max	
А	1,30	1,45	
В	1,15	1,35	
С	-	0,40	
D	0,10	0,50	
E	-	0,30	
F	0,06	0,10	
G	5,50	-	
Н	0,40	0,60	

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